

L Number	Rits	Search Text	DB	Time stamp
1	652	257/415.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 14:05
2	585	257/419.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 14:05
3	38	257/424.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 14:05
-	161	257/254.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:14
-	9	((257/254.ccls. and (gate near3 oxide)) and acceleration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:12
-	2	((257/254.ccls. and (gate near3 oxide)) and acceleration) and spring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:12
-	10	257/254.ccls. and acceleration and spring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:15
-	8	(257/254.ccls. and acceleration and spring) not ((257/254.ccls. and (gate near3 oxide)) and acceleration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:19
-	12153	acceleration same switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 14:48
-	21	(acceleration same switch) and ((gate near5 (oxide or insulator)) and (drain or source))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/12 18:45
-	11	((acceleration same switch) and ((gate near5 (oxide or insulator)) and (drain or source))) and spring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:21
-	24	(acceleration same switch) and (gate near5 (oxide or insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:22
-	11	((acceleration same switch) and (gate near5 (oxide or insulator)) ) and spring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:31
-	363	(acceleration same switch) and gate and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:57

-	330	((acceleration same switch) and gate and drain) and source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/05 16:58
-	312	((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and gate near5 (oxide or insulator)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/05 16:59
-	0	(((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator))) ) and spring) not (((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/05 17:44
-	183	(((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator))) ) not (((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator))) ) and spring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/05 17:52
-	160	257/254.ccls. not ((acceleration same switch) and (gate near5 (oxide or insulator)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/05 17:53
-	15	(257/254.ccls. and (gate near3 oxide)) not (((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/05 17:53
-	5	((US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.)	USPAT	2003/02/06 13:00
-	5	((US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.)	USPAT	2003/02/06 12:58
-	5	((US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.)	USPAT	2003/02/06 12:58
-	1	("5619050").PN.	USPAT	2003/02/06 12:59
-	1	((US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.) and (silicon near dioxide)	USPAT	2003/02/06 13:03
-	1	((US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.) and (silicon near dioxide)	USPAT	2003/02/06 13:03
-	13	((acceleration same switch) and (gate near5 (oxide or insulator))) not (((acceleration same switch) and (gate near5 (oxide or insulator))) and spring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/06 13:05
-	0	((((acceleration same switch) and (gate near5 (oxide or insulator))) not (((acceleration same switch) and (gate near5 (oxide or insulator))) and spring) and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/06 13:05
-	15	257/254.ccls. and (gate near3 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/06 13:05

-	4	(257/254.ccls. and (gate near3 oxide)) and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 15:29
-	129	(((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator))) ) ) and spring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:10
-	0	(((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator))) ) ) and spring and (silicon near3 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:11
-	1	(((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator))) ) ) and spring and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:11
-	238	73/514.36.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:11
-	193	73/514.36.ccls. and (acceleration or pressure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:12
-	4	(73/514.36.ccls. and (acceleration or pressure)) and gate and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:12
-	1	("5627397").PN.	USPAT	2003/02/06 14:34
-	2190	((acceleration same switch) and (semiconductor or ic or (integrated near2 circuit) or chip or die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 14:50
-	1458	((acceleration same switch) and (semiconductor or ic or (integrated near2 circuit) or chip or die)) and (source or drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/12 18:34
-	167	257/254.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 15:29
-	818	257/417.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 15:29
-	243	257/418.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 15:30
-	157	257/420.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 14:05
-	103	73/514.21.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 15:30

-	1508	((acceleration same switch) and (semiconductor or ic or (integrated near2 circuit) or chip or die)) and (source or drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/12 18:35
-	26	{acceleration same switch} and {(gate near5 (oxide or insulator)) and (drain or source)}	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/12 18:45